

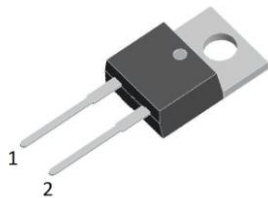
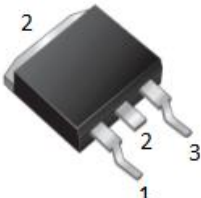
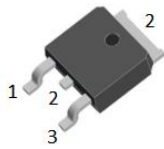
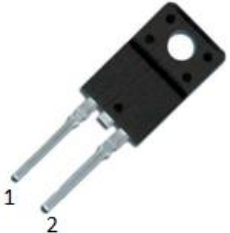
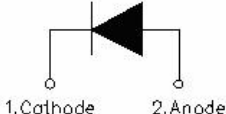
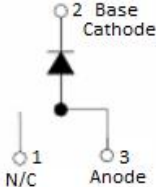
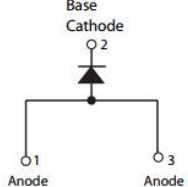
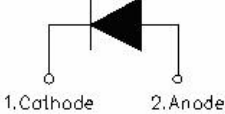
## ST10120/STB10120/STF10120/STD10120 SCHOTTKY RECTIFIER

### Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

### Features

- 150 °C T<sub>J</sub> operation
- Ultralow forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Trench MOS Schottky technology
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

ST10120	STB10120	STD10120	STF10120
			
			
TO-220AC	D <sup>2</sup> PAK	DPAK	ITO-220AC

### Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	120	V
Average Rectified Forward Current	I <sub>F(AV)</sub>	50% duty cycle @T <sub>c</sub> =100°C, rectangular wave form	10	A
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3ms, Half Sine pulse, T <sub>c</sub> = 25 °C	150	A

### Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 5A, Pulse, T <sub>J</sub> = 25 °C	0.60	-	V
		@ 10A, Pulse, T <sub>J</sub> = 25 °C	0.81	0.90	V
	V <sub>F2</sub>	@ 5A, Pulse, T <sub>J</sub> = 125 °C	0.50	-	V
		@ 10A, Pulse, T <sub>J</sub> = 125 °C	0.61	0.72	V
Reverse Current*	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 25 °C	0.02	0.7	mA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 125 °C	5	45	mA

\* Pulse width < 300 μs, duty cycle < 2%

### Thermal-Mechanical Specifications:

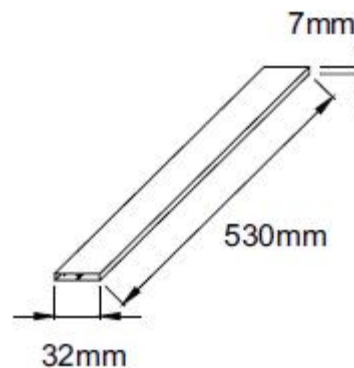
Characteristics	Symbol	ST10120	STB10120	STD10120	STF10120	Units
Junction Temperature	T <sub>J</sub>	-55 to +150				°C
Storage Temperature	T <sub>stg</sub>	-55 to +150				°C
Typical Thermal Resistance Junction to Case	R <sub>θJC</sub>	2.8	2.8	2.0	5.5	°C/W
Case Style		TO-220AC/ D <sup>2</sup> PAK/ DPAK/ ITO-220AC				

### Tube Specification

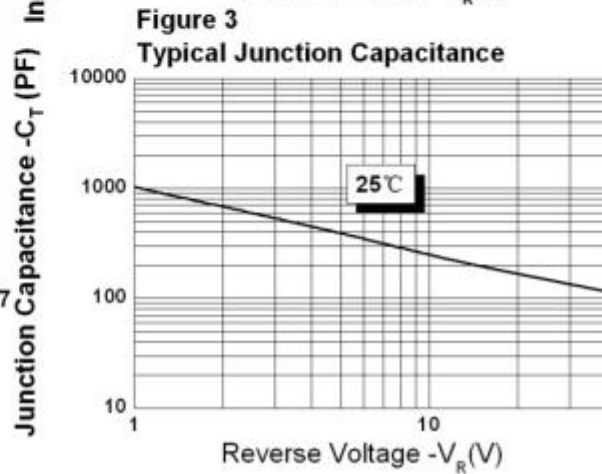
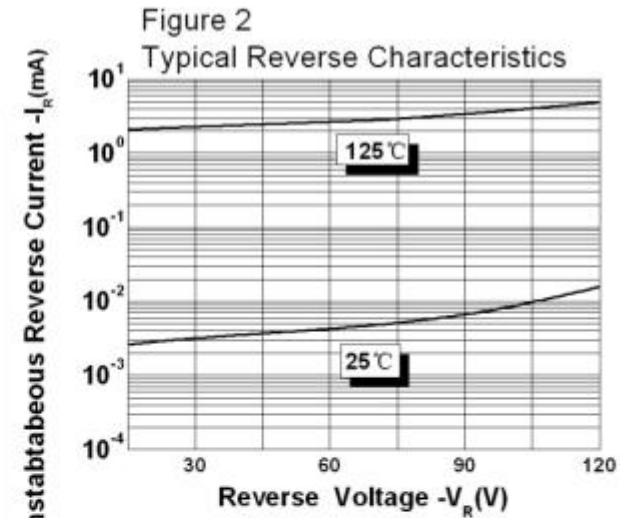
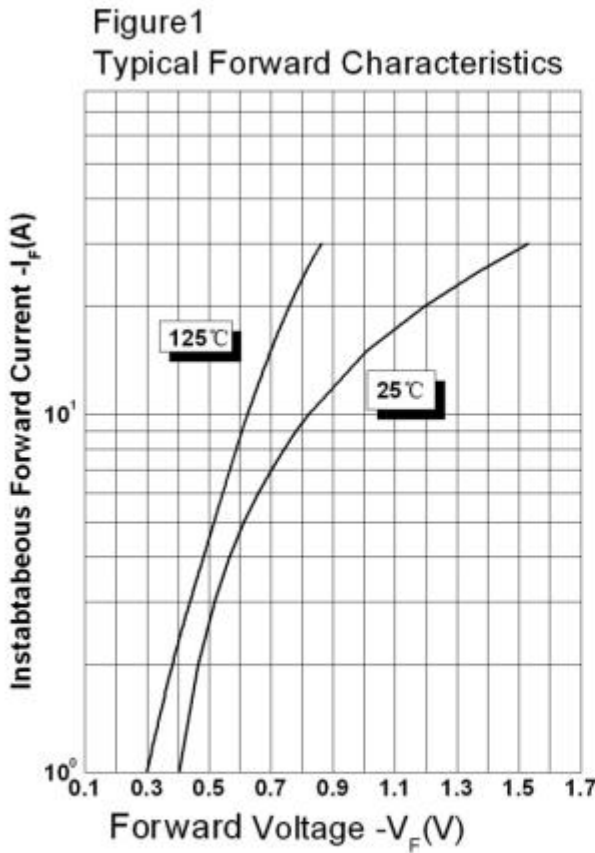
Device	Package	Weight	Shipping
ST10120	TO-220AC	1.6g	50pcs / tube
STB10120	D <sup>2</sup> PAK	1.85g	800pcs / reel
STD10120	DPAK	0.39g	2500pcs / reel
STF10120	ITO-220AC	1.6g	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

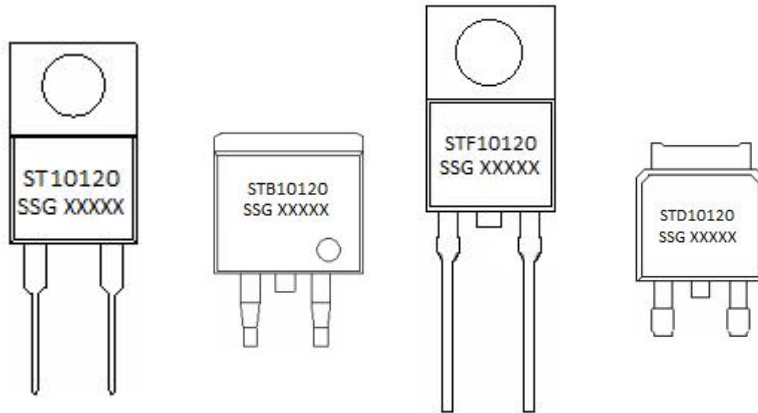
### Tube Specification(TO-220AC/ITO-220AC)



**Ratings and Characteristics Curves**



### Marking Diagram

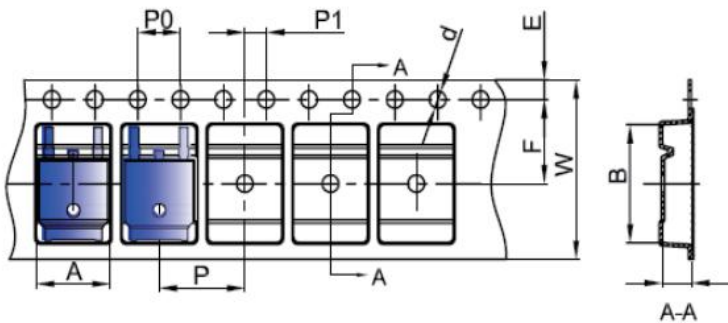


Where XXXXX is YYWWL

ST = Device Type  
B/D/F = Package type  
10 = Forward Current (10A)  
120 = Reverse Voltage (120V)  
SSG = SSG  
YY = Year  
WW = Week  
L = Lot Number

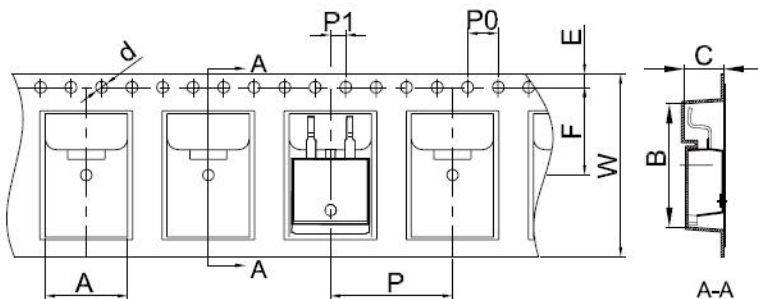
**Cautions:** Molding resin  
Epoxy resin UL:94V-0

### Carrier Tape Specification DPAK



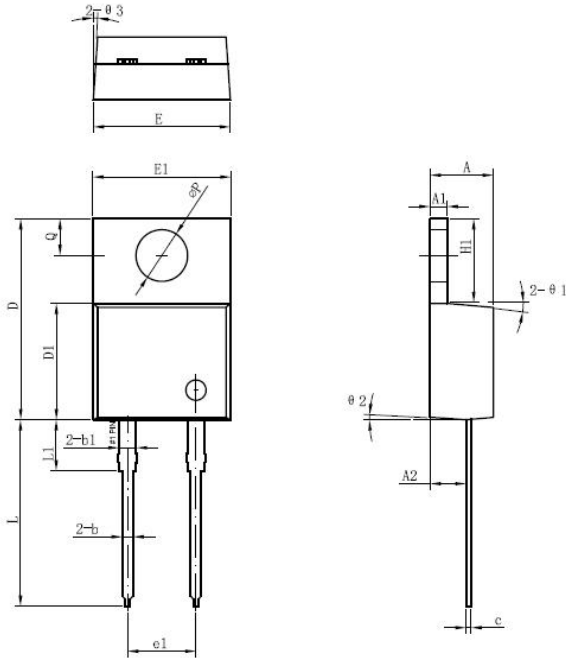
SYMBOL	Millimeters	
	Min.	Max.
A	6.80	7.00
B	10.40	10.60
C	2.60	2.80
d	Φ1.45	Φ1.65
E	1.65	1.85
F	7.40	7.60
P0	3.90	4.10
P	7.90	8.10
P1	1.90	2.10
W	15.90	16.30

### Carrier Tape Specification D<sup>2</sup>PAK



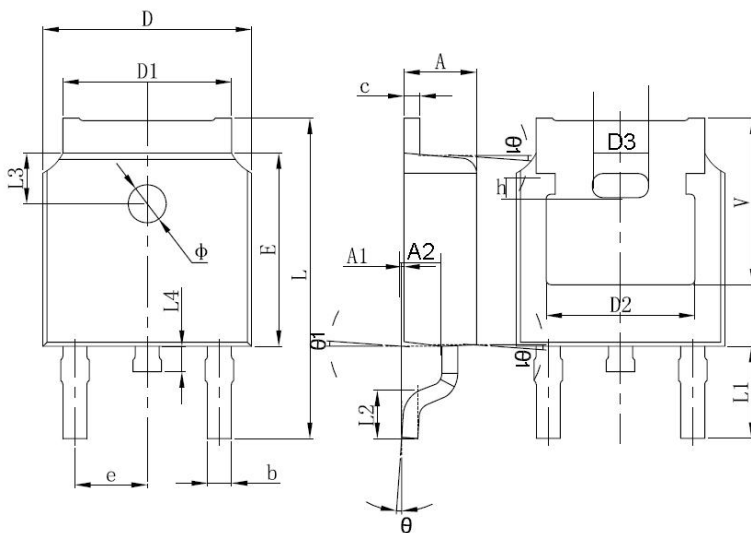
SYMBOL	Millimeters	
	Min.	Max.
A	10.70	10.90
B	16.03	16.23
C	5.11	5.31
d	1.45	1.65
E	1.65	1.85
F	11.40	11.60
P0	3.90	4.10
P	15.90	16.10
P1	1.90	2.10
W	23.90	24.30

**Mechanical Dimensions TO-220AC**



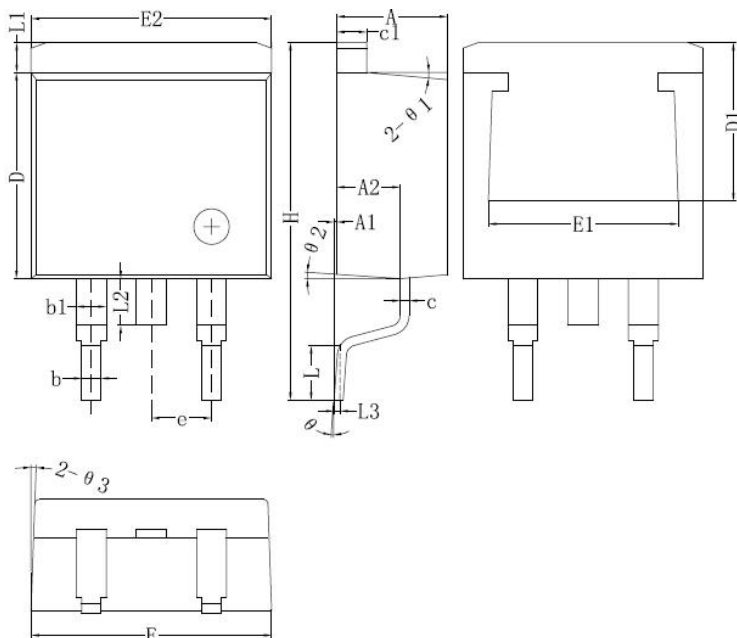
Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	4.47	4.70	4.85
A1	1.17	1.27	1.37
A2	2.52	2.69	2.89
b	0.71	0.81	0.96
b1	1.17	1.27	1.37
c	0.31	0.38	0.61
D	14.64	14.94	15.24
D1	8.50	8.07	8.90
E	10.01	10.16	10.31
E1	9.98	10.18	10.38
e1	4.98	5.08	5.18
H1	6.04	6.24	6.44
L	13.00	13.86	14.08
L1	3.56	3.80	3.96
ΦP	3.74	3.84	4.04
Q	2.54	2.74	2.94
Θ1		5°	
Θ2		4°	
Θ3		4°	

**Mechanical Dimensions DPAK**



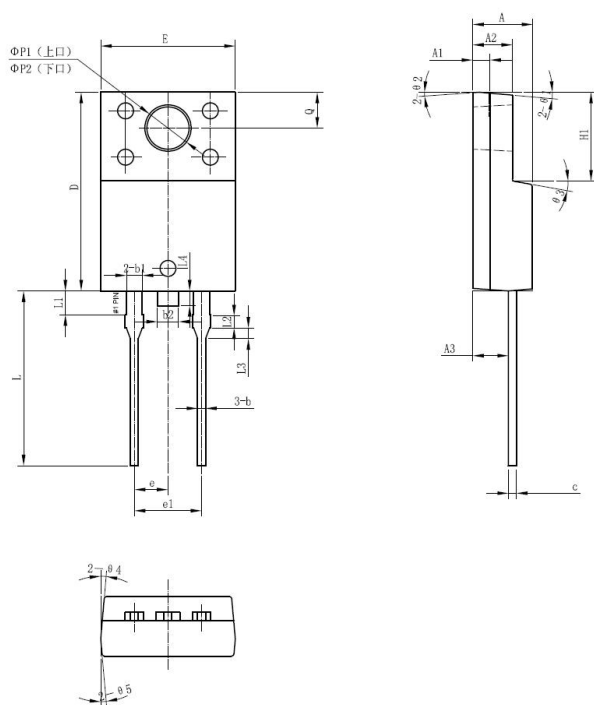
SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.20	2.40	0.087	0.094
A1	0.00	0.127	0.000	0.005
b	0.66	0.86	0.026	0.034
c	0.46	0.60	0.018	0.024
D	6.50	6.70	0.256	0.264
D1	5.13	5.46	0.202	0.215
D2	4.83 REF.		0.190 REF.	
E	6.00	6.20	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.70	10.40	0.381	0.409
L1	2.90 REF.		0.144 REF.	
L2	1.40	1.70	0.055	0.067
L3	1.60 REF.		0.063 REF.	
L4	0.60	1.00	0.024	0.039
Φ	1.10	1.30	0.043	0.051
Θ	0°	8°	0°	8°
h	0.00	0.30	0.000	0.012
V	5.35 REF.		0.211 REF.	

**Mechanical Dimensions D<sup>2</sup>PAK**



Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	4.47	4.70	4.85
A1	0	0.10	0.25
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1	1.17	1.27	1.37
c	0.31	0.38	0.61
c1	1.17	1.27	1.37
D	8.50	8.70	8.90
D1	6.40		
E	10.01	10.16	10.31
E1	7.6		
E2	9.98	10.08	10.31
e		2.54	
H	14.6	15.1	15.6
L	2.00	2.30	2.74
L1	1.12	1.27	1.42
L2	1.30		2.20
L3		0.25BSC	
e	0	-	8°
e1		5°	
e2		4°	
e3		4°	

**Mechanical Dimensions ITO-220AC**



SYMBOL	Dimensions in millimeters		
	Min.	Typical	Max.
A	4.30	4.50	4.70
A1	1.10	1.30	1.50
A2	2.80	3.00	3.20
A3	2.50	2.70	2.90
b	0.50	0.60	0.75
b1	1.10	1.20	1.35
b2	1.50	1.60	1.75
c	0.50	0.60	0.75
D	14.80	15.00	15.20
E	9.96	10.16	10.36
e	-	2.55	-
e1	5.00	5.10	5.16
H1	6.50	6.70	6.90
L	12.70	13.20	13.70
L1	1.60	1.80	2.00
L2	0.80	1.00	1.20
L3	0.60	0.80	1.00
L4	-	1.10	1.50
ΦP1(上口)	3.30	3.50	3.70
ΦP2(下口)	2.99	3.19	3.39
Q	2.50	2.70	2.90
θ1		5°	
θ2		4°	
θ3		10°	
θ4		5°	
θ5		5°	



ST10120  
STB10120  
STD10120  
STF10120

**Technical Data**  
**Data Sheet N1360, Rev. A**



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